

Spin singlet small bipolarons in Nb-doped BaTiO₃

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The magnetic susceptibility and electrical resistivity of n-type BaTi_{1-x}Nb_xO₃ have been measured over a wide temperature range. It is found that, for $0 < x < 0.2$, dopant electrons form immobile spin singlet small bipolarons with binding energy around 110 meV. For $x = 0.2$, a maximum in the electrical resistivity around 15 K indicates a crossover from band to hopping transport of the charge carriers, a phenomenon expected but rarely observed in real polaronic systems.

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The theoretical treatment of itinerant carriers interacting with a strongly polarizable lattice has been conducted for over 50 years, resulting in a variety of different models. Depending on the degree of electron-lattice interaction, these models can be roughly divided into two main groups. The first [1, 2] treats the electron as a Bloch-wave-like delocalized particle called a Fröhlich or large polaron. The second [3, 4] assumes an extreme localization of the itinerant electron within one or several lattice sites (i.e., a small polaron, SP) accompanied by a strong local lattice deformation. It is expected that under certain conditions, polarons can pair to form large/small bipolarons, BP [5, 6]. Although not without controversy [7], several authors suggest [6] that Bose-Einstein condensation of bipolarons may result in high- T_c superconductivity.

Evidence of a strong electron-lattice interaction has been accumulating for ATiO₃, where $A = \text{Ba}$ or Sr [8, 9]. These are textbook examples of crystals having a simple perovskite structure and high static dielectric constant furnished by a soft phonon mode. Stoichiometric ATiO₃ are band gap insulators. Donor doping or reduction in an oxygen-deficient atmosphere results an n-type material with unconventional electronic conductivity where the carriers move within a very soft and deformable lattice. In SrTiO₃, the overlap between the Ti-Ti 3d t_{2g} orbitals is strong enough to prevent the localization of the itinerant electrons which then form large polarons. As a result, n-type SrTiO₃ shows metallic conductivity with an enhanced effective electron mass m^* of $6m_e$ to $14m_e$ [10, 11]. It has been argued that, at low temperatures, large polarons in n-type SrTiO₃ condense into the large BPs responsible for superconductivity below 0.6 K [11].

The lattice constant of cubic BaTiO₃ ($a = 0.4005$ nm) is 2.5% larger than that of SrTiO₃ ($a = 0.3905$ nm). This small increase in a causes a dramatic difference in the electronic properties of the two compounds. Unlike n-type SrTiO₃, the conductivity of n-type BaTiO₃ shows insulating behavior with the low conductivity attributed to the thermally activated hopping of strongly localized electrons (i.e., small polarons) between neighboring Ti

sites. Gerthsen *et al.* [12] explained the mid-infrared reflectance of n-type BaTiO₃ in terms of the SP absorption model. In accord with the hopping transport of SPs, Bursian *et al.* [13] found that the Seebeck coefficient of weakly-doped n-type BaTiO₃ is temperature independent above 300 K. Direct evidence of the self-trapped Ti³⁺ SP was provided by ESR studies of acceptor depleted BaTiO₃ [14]. Nevertheless, the SP interpretation of the electronic properties of BaTiO₃ is far from uncontroversial. Two major points of disagreement are the similarity in the Hall and drift mobilities ($\mu_{\text{Hall}} \approx \mu_{\text{drift}} \approx 0.2 \text{ cm}^2/\text{V s}$ at 300 K) which, according to the SP model, should satisfy $\mu_{\text{Hall}} \gg \mu_{\text{drift}}$ [15], and the large difference between the optical and thermal activation energies ($E_{\text{op}} = 500 - 600$ meV, $E_{\text{th}} = 23$ meV) of the proposed SPs, that should satisfy $E_{\text{op}} = 4E_{\text{th}}$ [16].

In our opinion, the polaronic approach to understanding the unusual properties of n-type BaTiO₃ requires that the possibility of electron pairing be taken into account. The coupling of electrons into Anderson-type *on-site* spin singlet Ti²⁺ small bipolarons according to $\text{Ti}^{4+} + 2e^- \rightarrow \text{Ti}^{2+}$ was first postulated by Moizhes and Suprun [17]. Later, the idea of BPs in BaTiO₃ was supported by Lenjer and co-workers [9], who observed an unexpected increase in the Ti³⁺ ESR signal with temperature. This observation led them to suggest that, due to the high correlation energy that sets the energy cost for a double occupancy of the Ti²⁺ ion, the symmetry of the BP is rather of the *inter-site*, i.e., Heitler-London type, where the electron pair is localized at two neighboring Ti³⁺ ions according to $2\text{Ti}^{4+} + 2e^- \rightarrow 2\text{Ti}^{3+}$.

The central question addressed in this Letter is whether the Ti³⁺ $S = \frac{1}{2}$ small polarons in n-type BaTiO₃ remain isolated at $T = 0$ K or if they pair into spin singlet $S = 0$ bipolarons. We also report on the physical properties of the BPs in n-type BaTiO₃, as revealed by magnetic and electrical measurements.

Polycrystalline BaTi_{1-x}Nb_xO₃ samples with $0 \leq x \leq 0.2$ were prepared by solid state reaction from high purity 99.99+% BaCO₃, TiO₂, and Nb₂O₅. Sintering was performed in forming gas (3% H₂/97% N₂) to ensure electronic rather than cation vacancy compensation of the

Nb dopant [18]. Phase purity of the ceramics was confirmed by powder x-ray diffraction and energy dispersive x-ray microanalysis with no evidence of secondary phases up to $x = 0.2$. According to x-ray photoelectron spectroscopy measurements, charge compensation in the sintered $\text{BaTi}_{1-x}\text{Nb}_x\text{O}_3$ samples is accomplished by the formation of Ti^{3+} ions while the Nb ions remain predominantly in the 5+ oxidation state.

Assuming strong localization of excess electrons on isolated Ti^{3+} ions down to 0 K (SP ground state), the magnetic susceptibility should decrease with temperature in accordance with the Curie law,

$$\chi_{\text{para}} = \frac{N_A p^2 \mu_B^2 c_P}{3k_B T}, \quad (1)$$

where N_A is the Avogadro number, p is the effective magnetic moment in Bohr magnetons (μ_B), k_B is the Boltzmann constant, T is the temperature and c_P is the concentration of small polarons. Figure 1 shows the temperature dependence of the molar magnetic susceptibility, χ_M , of the $\text{BaTi}_{1-x}\text{Nb}_x\text{O}_3$ ceramics in the 2 – 800 K temperature range. It is obvious that the $\chi_M(T)$ data do not support a simple SP scenario. The observed

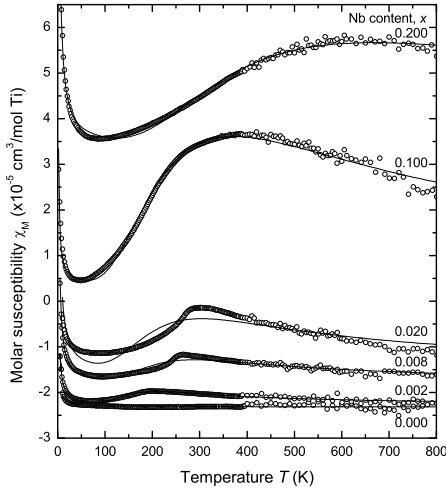


FIG. 1: Magnetic susceptibility per mole of Ti of the $\text{BaTi}_{1-x}\text{Nb}_x\text{O}_3$ ceramics with $x = 0, 0.002, 0.008, 0.020, 0.100$ and 0.200 . Solid lines are fits to the data as described in the text.

anomalous increase in χ_M at intermediate temperatures is associated with the breaking up of spin singlet BPs. An overall increase in χ_M with dopant concentration is attributed to the formation of the BP band with associated van Vleck paramagnetism. To fit the data we apply Emin's formalism [19] for dissociation of small BPs in a weak magnetic field ($g\mu_B B \ll 2k_B T$). According to

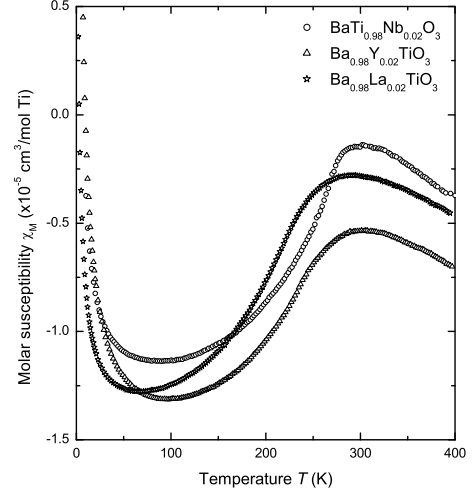


FIG. 2: Comparison of the magnetic susceptibility of Nb-doped BaTiO_3 with that of BaTiO_3 doped with donors having a stable oxidation state (Y^{3+} and La^{3+}). All three curves reveal a magnetic anomaly.

Emin, the concentration of SPs, c_P , produced by thermal dissociation of BPs is given by

$$c_P = \frac{1 - (1 - x) \sqrt{1 + [x(2 - x)/(1 - x)^2] e^{\varepsilon_b/k_B T}}}{1 - e^{\varepsilon_b/k_B T}}, \quad (2)$$

where x is the concentration of the Nb^{5+} dopant and ε_b is the BP binding energy, i.e., the energy required to split the BP into two SPs. The data in Fig.1 were fitted with the general formula

$$\chi_M = \chi_{\text{dia}} + \chi_{\text{VV}} + \frac{A}{T} + \chi_{\text{para}}, \quad (3)$$

where $\chi_{\text{dia}} = -2.32 \times 10^{-5} \text{ cm}^3/\text{mol}$ is the diamagnetic susceptibility of the undoped, stoichiometric BaTiO_3 , χ_{VV} is the temperature independent van Vleck paramagnetic contribution, and A accounts for impurity-related paramagnetism dominant at $T < 40 \text{ K}$.

The van Vleck term is given by

$$\chi_{\text{VV}} = \frac{2N_A x |\langle l | \mu_z | 0 \rangle|^2}{\Delta} \quad (4)$$

where $\langle l | \mu_z | 0 \rangle$ is a non-diagonal matrix element of the magnetic moment operator connecting the BP ground state 0 with the excited state l of energy $\Delta = E_l - E_0$ above the ground state.

The results of the fit are shown as solid lines in Fig.1. The fitting parameters are summarized in Table I. A somewhat larger value of A for the $x = 0.2$ sample is attributed to the partial compensation of the Nb dopant by paramagnetic cation vacancies as we approach the solubility limit of Nb in BaTiO_3 . In agreement with Eq.4,

χ_{VV} is found to scale linearly with dopant concentration. Good fits were obtained for $x = 0, 0.002, 0.1$ and 0.2 and somewhat worse fits for $x = 0.008$ and 0.02 . We can explain the poor fit at intermediate dopant concentrations since, while fitting the data, we have assumed a constant ε_b and χ_{VV} for the entire temperature range. It is known, however, that undoped BaTiO_3 exists in four crystallographic forms [20]: rhombohedral at $T < 200$ K, orthorhombic at $200 \text{ K} < T < 270$ K, tetragonal at $270 \text{ K} < T < 393$ K and cubic at $393 \text{ K} < T < 1670$ K. Since both ε_b and χ_{VV} depend on the crystal symmetry, the use of single values of ε_b and χ_{VV} for $x = 0.008$ and 0.02 gives only marginally satisfactory results. At the lowest dopant concentration ($x = 0.002$), 70% of the BPs are already dissociated into SPs at 200 K, i.e., fully within the rhombohedral phase. As a result, this fit is good in spite of the single values of ε_b and χ_{VV} used. Doping with Nb results in a significant lowering of the phase transition temperatures in BaTiO_3 [21]. Indeed, low-temperature x-ray analysis of the $x \geq 0.1$ samples confirmed that they remain cubic down to at least 20 K. Hence, the use of single values of ε_b and χ_{VV} produces a good fit also in these cases. The data show that in the doping range covering two orders of magnitude, the bipolaron binding energy is of the order of 110 meV. For the most highly doped sample ($x = 0.2$), the bipolaron binding energy (172 meV) is found to be rather high. This may be due to the solubility limit of donor atoms and/or BP overcrowding effects.

TABLE I: Fitting parameters for χ_M of $\text{BaTi}_{1-x}\text{Nb}_x\text{O}_3$.

x	$\chi_{VV} \times 10^5$ [cm ³ /mol]	$A \times 10^5$ [cm ³ K/mol]	ε_b [meV]	p
0.000	0	2.16	—	—
0.002	0.02	5.73	106	0.57
0.008	0.47	11.73	122	0.46
0.020	0.73	16.64	111	0.46
0.100	2.68	5.96	105	0.42
0.200	5.69	22.5	172	0.36

One might argue, however, that the BP interpretation of the χ_M anomaly is not convincing enough, and that thermal activation of intrinsic or extrinsic lattice defects may generate similar effects. Let us address this crucial argument in detail. Since no χ_M anomaly is observed in undoped, stoichiometric BaTiO_3 , the possibility of the $S = 0 \rightarrow S = \frac{1}{2}$ activation of any supposed extrinsic impurities can be ruled out. According to the point defect chemistry of BaTiO_3 , the Nb^{5+} dopant is compensated by barium or titanium vacancies at high oxygen partial pressures (P_{O_2}) and by electrons at low P_{O_2} [18]. Since the samples were prepared at low P_{O_2} , the concentra-

tion of cation vacancies is negligible. However, even if a small amount of cation vacancies were still present in the heavily doped samples, their thermal activation energy is at least five times higher than ε_b [18]. It is quite possible that oxygen vacancies (V_O) are present in the samples. According to recent calculations [22], these vacancies will form a $[\text{Ti}^{3+}-V_O-\text{Ti}^{3+}]$ neutral complex defect. In fact, the $[\text{Ti}^{3+}-V_O-\text{Ti}^{3+}]$ complex is nothing other than the small BP bound to the oxygen vacancy, although in this case the electrons are localized on the Ti $3z^2-r^2$ orbitals [23]. Activation of this defect according to $[\text{Ti}^{3+}-V_O-\text{Ti}^{3+}] \rightarrow [\text{Ti}^{3+}-V_O] + \text{Ti}^{3+}$ may indeed cause a χ_M anomaly similar to that observed in Fig.1. However, donor doping always decreases the concentration of V_O [18]. Hence one would expect a decrease in the χ_M anomaly with increasing doping, which is opposite to what is seen in our results. Finally, we rule out the possibility that the χ_M anomaly is associated with a change in the ionization state of Nb^{5+} according to $\text{Nb}^{5+} + \text{Ti}^{4+} \rightarrow \text{Nb}^{5+} + \text{Ti}^{3+}$ since Fig.2 shows similar magnetic anomalies occurring when electrons are introduced into BaTiO_3 by donors having a stable oxidation state (Y^{3+} and La^{3+}).

Recently, magnetic susceptibility measurements have been made on several $3d^1$ titanates including MgTi_2O_4 , $\text{NaTiSi}_2\text{O}_6$ and $\text{LiTiSi}_2\text{O}_6$ [24]. It was found that magnetic anomalies in all the above compounds were associated with the formation of spin-singlet $\text{Ti}^{3+}-\text{Ti}^{3+}$ pairs. In contrast to the above compounds, the formation of BPs in n-type BaTiO_3 is not driven by a change in the crystal symmetry, as revealed in the samples with $x \geq 0.1$. It also appears that pairing of the electrons occurs even for very diluted $3d^{0+\delta}$ ($\delta \ll 1$) electronic concentrations as in the case of $x = 0.002$.

In view of the heated debate regarding the possibility of the existence of *mobile* small BPs [7], we have also examined the electronic behavior of n-type BaTiO_3 . According to the resistivity data shown in Fig.3, the ground state of n-type BaTiO_3 is insulating throughout the $0 < x < 0.2$ doping range [25] and therefore comprises immobile small BPs. The total conductivity can be expressed as a sum of polaronic, σ_P , and bipolaronic, σ_{BP} , conductivities

$$\sigma = \sigma_P + \sigma_{BP} = e c_P \mu_P + 2e \frac{x - c_P}{2} \mu_{BP}, \quad (5)$$

where μ_P and μ_{BP} are the drift mobilities of SPs and BPs, respectively. We assume, in accordance with Ref. [19], that for a low doping level the main contribution to σ comes from the SPs that are formed by thermal dissociation of the BPs and that σ_{BP} is negligible due to the large effective mass and very low mobility of BPs. Then, in the case of non-adiabatic hopping of SPs [29],

$$\sigma \approx e c_P \mu_P \propto \frac{1}{T^{1.5}} \exp \left[-\frac{\varepsilon_b + E_{th}}{k_B T} \right]. \quad (6)$$

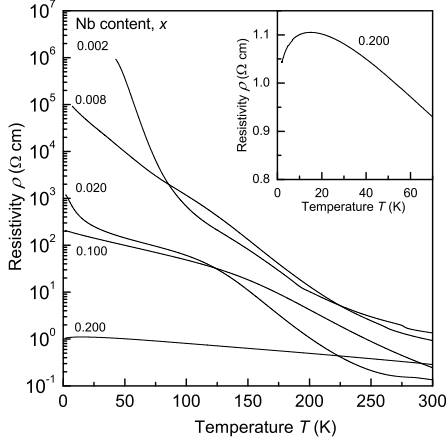


FIG. 3: Electrical resistivity of the $\text{BaTi}_{1-x}\text{Nb}_x\text{O}_3$ ceramics with $x = 0.002, 0.008, 0.020, 0.100$ and 0.200 . The inset highlights the crossover from band to hopping conduction in the $x = 0.200$ sample.

Taking $E_{\text{th}} = 23$ meV from Ref. [16] and ε_b from Table I, the total activation energy of conductivity, $\varepsilon_b + E_{\text{th}}$, should be around 135 ± 10 meV at high temperatures, with a slight deviation for the $x = 0.2$ sample. Indeed the resistivity data confirm that all but the $x = 0.2$ sample show activated conductivity above $T \approx 155$ K with an activation energy of ca. 135 meV as shown in Fig. 4. The strong downturn from Arrhenius behavior for $T < 155$ K is due to an enhancement of the mobility by quantum lattice fluctuations [26]. As the dopant concen-

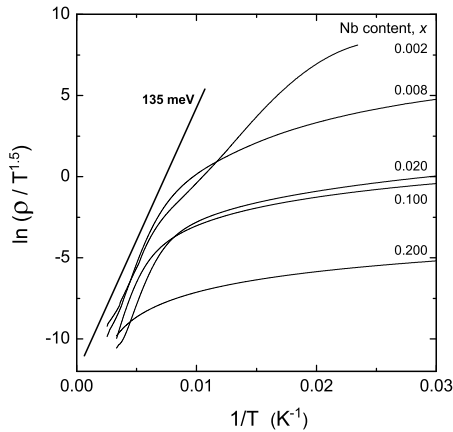


FIG. 4: Arrhenius plot of the resistivity of the $\text{BaTi}_{1-x}\text{Nb}_x\text{O}_3$ ceramics assuming non-adiabatic hopping of the localized carriers.

tration increases, the σ_{BP} contribution can no longer be neglected. In fact, the sample with the highest doping level ($x = 0.2$) shows a strong conductivity enhancement at low temperature, with a maximum in ρ at $T = 15$ K as shown in the inset of Fig. 3. According to the SP theory, the resistivity maximum is expected [26] but rarely observed in real polaronic systems [27]. In our case, it is associated with a crossover from the coherent transport of BPs within the bipolaron band below 15 K to the incoherent (i.e., hopping) transport of BPs above 15 K. We should stress here that this phenomenon is not unique to Nb-doped samples and has also been observed in La-doped BaTiO_3 .

Finally, let us compare the thermal dissociation energy of BPs, ε_b , obtained in this work with literature data on the infra-red absorption band of n-type BaTiO_3 centered at $E_{\text{op}} = 500 - 600$ meV [28, 29]. Optical absorption of BPs involves the splitting of the two electrons and transfer of one of them to the next neighboring site. According to Emin [30], this process would require an energy of $E_{\text{op}} \approx 4\varepsilon_b$. Taking ε_b data for weakly doped samples ($x < 0.02$) from Table I, the optical absorption due to the BPs would produce a band centered at 420 – 490 meV, which is in reasonable agreement with the literature data. A BP-associated optical absorption is expected to be strongly temperature dependent since the concentration of the BPs decreases with temperature. An alternative source of the mid-infrared absorption band in n-type BaTiO_3 could be the $d_{xy} \rightarrow d_{xz}, d_{yz}$ orbital (intra-band) excitations. Formation of the SP removes the three-fold t_{2g} orbital degeneracy in BaTiO_3 due to the $T_2 \times e$ Jahn-Teller effect. According to ESR data, the energy associated with the orbital excitations within the t_{2g} band in n-type BaTiO_3 is around 400 – 536 meV [31]. In this case, however, the intensity and the energy maximum of the optical absorption should be temperature independent. Since there are no data on the temperature dependence of the mid-infrared band of n-type BaTiO_3 , the certain origin of this band remains unresolved.

In conclusion, as revealed by magnetic susceptibility data, “itinerant” electrons in $\text{BaTi}_{1-x}\text{Nb}_x\text{O}_3$ with $0 < x < 0.2$ form localized pairs with a spin singlet ground state. The binding energy of the BPs ranges from 105 meV to 122 meV depending on the dopant concentration. Electrical resistivity measurements show that, throughout this doping range, the BPs are *immobile*. A crossover from band to hopping transport is manifested by a resistivity maximum at $T = 15$ K in the most heavily doped ($x = 0.2$) sample investigated. This indicates that at rather high doping concentration, small BPs in BaTiO_3 become *mobile*. In a more general perspective, we speculate that BaTiO_3 and SrTiO_3 play host to the two extreme cases of the bipolaron ground state: the small BP in BaTiO_3 evolves into a large BP in SrTiO_3 . Hence, $\text{BaTiO}_3 - \text{SrTiO}_3$ may become a model system for studies of the physics of small and large BPs as it became a model sys-

tem for studies of soft mode behavior 50 years ago.

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